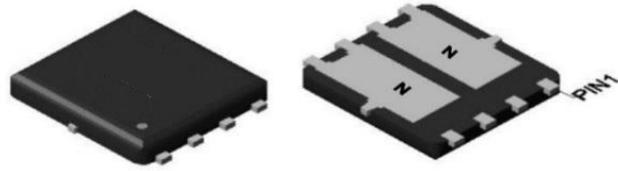
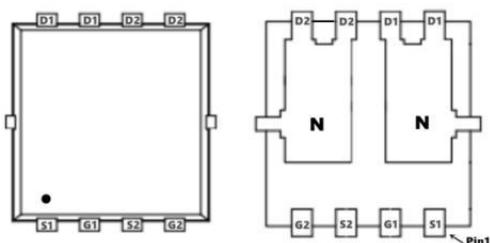


Description

The SX70H06NF uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = 60V$ $I_D = 70A$

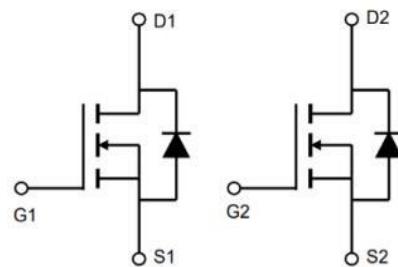
$R_{DS(ON)} < 10m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain source voltage	60	V
V_{GS}	Gate source voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous drain current	70	A
$I_D @ T_A=70^\circ C$	Continuous drain current	45	A
IDM	Pulsed drain current	280	A
$P_D @ T_A=25^\circ C$	Power dissipation	60	W
EAS	Single pulsed avalanche energy	30	mJ
TSTG	Storage Temperature Range	-55 to 150	°C
T_j	Operation and storage temperature	-55 to 150	°C
$R_{\theta JC}$	Thermal resistance, junction-case	2.1	°C/W
$R_{\theta JA}$	Thermal resistance, junction-ambient5)	25	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
BVDSS	Drain-source breakdown voltage	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	60	68		V
VGS(th)	Gate threshold voltage	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$	1.2	1.5	2.5	V
RDS(ON)	Drain-source on-state resistance	$V_{GS}=10\text{ V}$, $I_D=20\text{ A}$		7.5	10	$\text{m}\Omega$
RDS(ON)	Drain-source on-state resistance	$V_{GS}=4.5\text{ V}$, $I_D=10\text{ A}$		10	13	$\text{m}\Omega$
IGSS	Gate-source leakage current	$V_{GS}=\pm 20\text{ V}$			± 100	nA
IDSS	Drain-source leakage current	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$			1	μA
Ciss	Input capacitance	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$		1182.1		pF
Coss	Output capacitance			199.5		pF
Crss	Reverse transfer capacitance			4.1		pF
td(on)	Turn-on delay time	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $R_G=2\text{ }\Omega$, $I_D=10\text{ A}$		17.9		ns
tr	Rise time			4.0		ns
td(off)	Turn-off delay time			34.9		ns
tf	Fall time			5.5		ns
Qg	Total gate charge	$I_D=10\text{ A}$, $V_{DS}=50\text{ V}$, $V_{GS}=10\text{ V}$		18.4		nC
Qgs	Gate-source charge			3.3		nC
Qgd	Gate-drain charge			3.1		nC
Vplateau	Gate plateau voltage			2.8		V
Is	Diode forward current	VGS<Vth			60	A
ISP	Pulsed source current				180	
VSD	Diode forward voltage	$I_S=20\text{ A}$, $V_{GS}=0\text{ V}$			1.3	V
trr	Reverse recovery time	$I_S=10\text{ A}$, $dI/dt=100\text{ A}/\mu\text{s}$		41.8		ns
Qrr	Reverse recovery charge			36.1		nC
Irrm	Peak reverse recovery current			1.4		A

Note

1. Calculated continuous current based on maximum allowable junction temperature.
2. Repetitive rating; pulse width limited by max. junction temperature.
3. Pd is based on max. junction temperature, using junction-case thermal resistance.
4. $V_{DD}=50\text{ V}$, $R_G=50\text{ }\Omega$, $L=0.3\text{ mH}$, starting $T_j=25^\circ\text{C}$.
5. The value of R_{SDA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25^\circ\text{C}$.

Typical Characteristics

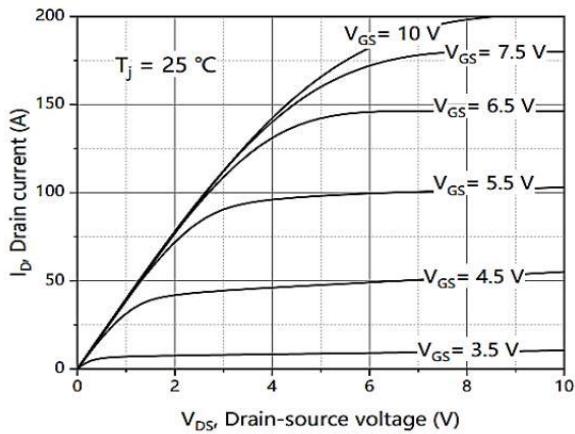


Figure 1. Typ. output characteristics

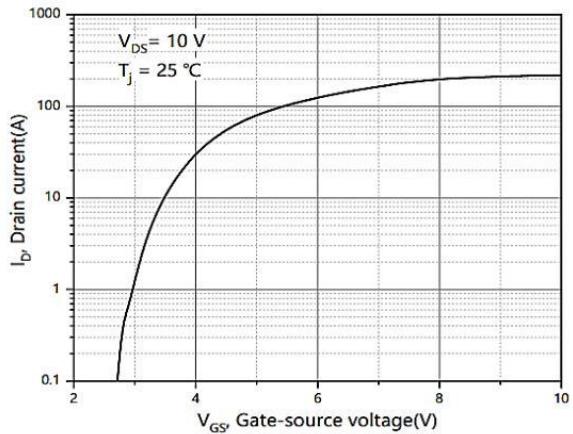


Figure 2. Typ. transfer characteristics

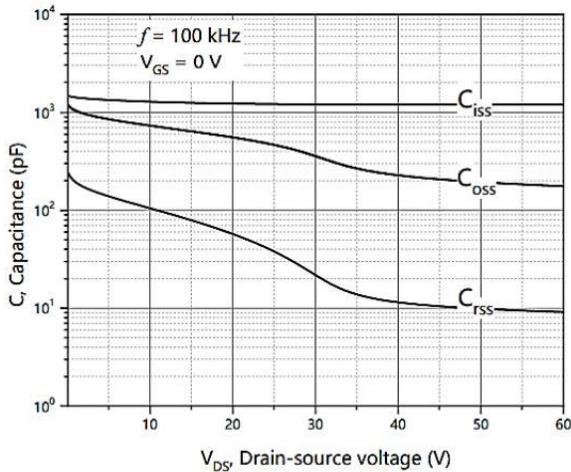


Figure 3. Typ. capacitances

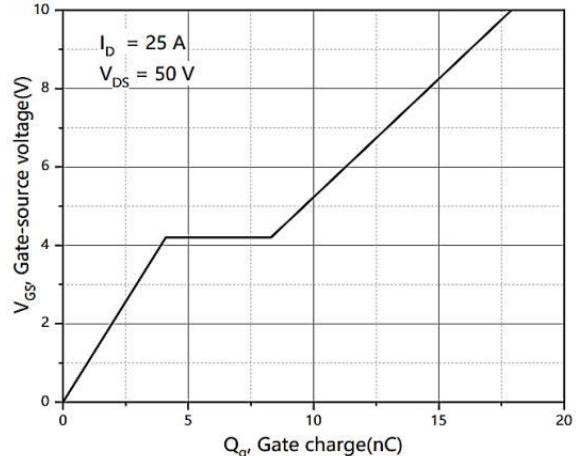


Figure 4. Typ. gate charge

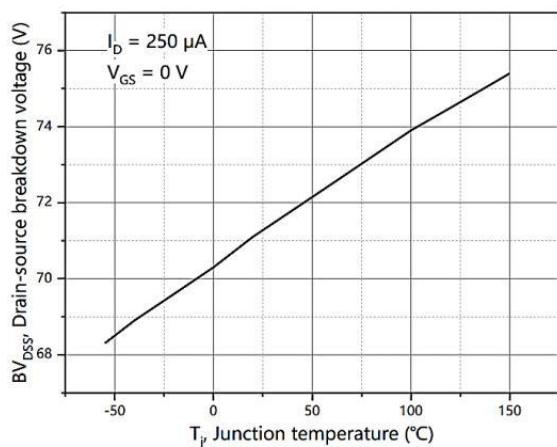


Figure 5. Drain-source breakdown voltage

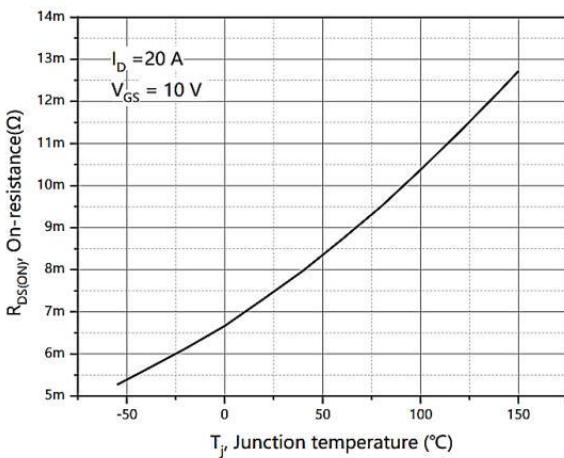


Figure 6. Drain-source on-state resistance

Typical Characteristics

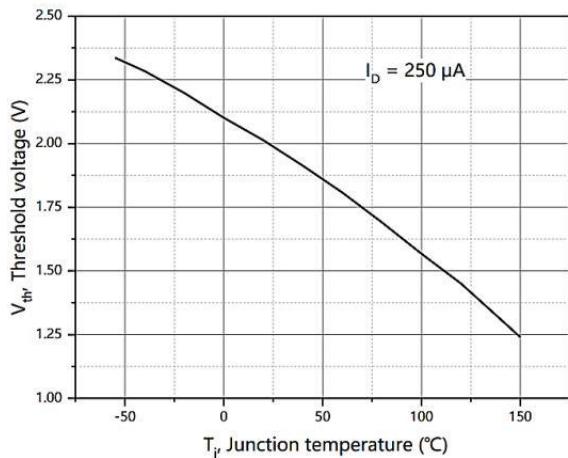


Figure 7. Threshold voltage

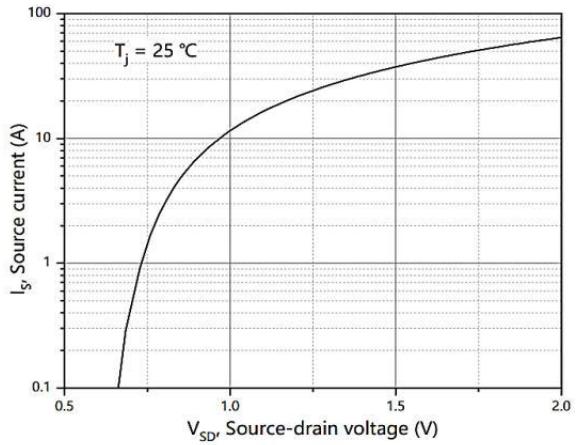


Figure 8. Forward characteristic of body diode

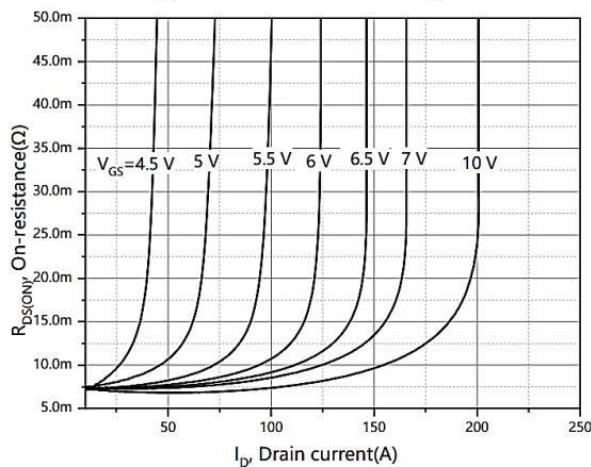


Figure 9. Drain-source on-state resistance

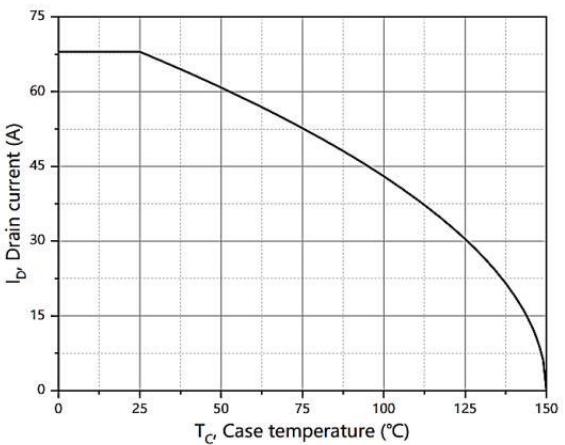


Figure 10. Drain current

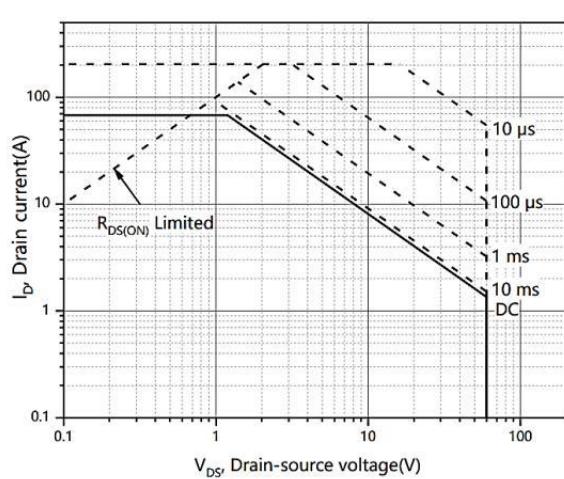


Figure 11. Safe operation area $T_c=25\text{ }^\circ\text{C}$

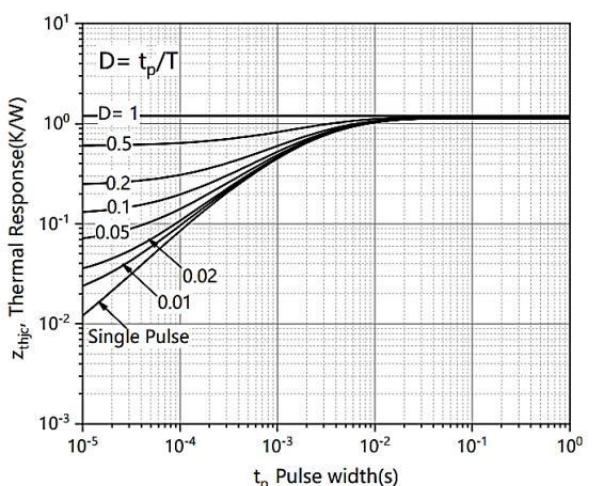
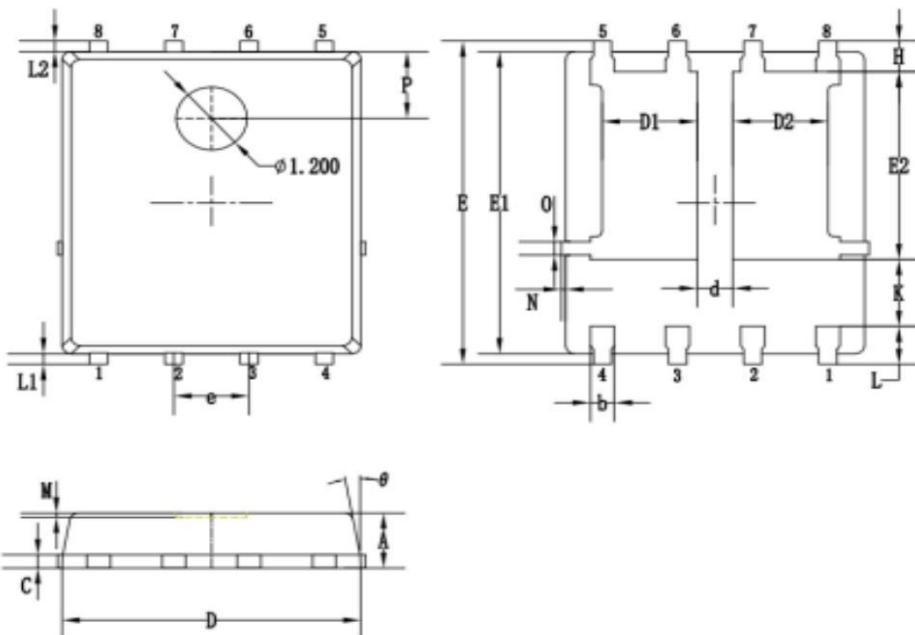


Figure 12. Max. transient thermal impedance

Package Mechanical Data-PDFN5*6-8L Double



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.9	1.05	1.2
b	0.35	0.4	0.5
C	0.2	0.25	0.35
D	4.9	5.05	5.2
D1/D2	1.51	1.61	1.71
d	0.5	0.6	0.7
E	6	6.15	6.3
E1	5.6	5.75	5.9
E2	3.47	3.57	3.67
e	1.27 BSC,		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
Θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000